

Tzer-En Nee

List of Publications by Year in descending order

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35
papers

148
citations

1478280

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all docs

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docs citations

35
times ranked

158
citing authors

#	ARTICLE	IF	CITATIONS
1	Thermophysical Characterization of Efficiency Droop in GaN-Based Light-Emitting Diodes. <i>Nanomaterials</i> , 2021, 11, 1449.	1.9	4
2	Lie symmetry analysis of the effects of urban infrastructures on residential property values. <i>PLoS ONE</i> , 2021, 16, e0255233.	1.1	3
3	Intensive measures of luminescence in GaN/InGaN heterostructures. <i>PLoS ONE</i> , 2019, 14, e0222928.	1.1	3
4	Investigation of the thermal photocarrier interactionâ€“recombination in ZnO nanostructures fabricated by the hydrothermal method. <i>Journal of Luminescence</i> , 2017, 190, 136-140.	1.5	5
5	Strain modulated defect luminescence in ZnO nanostructures grown on Si substrates. <i>Journal of Luminescence</i> , 2015, 168, 304-308.	1.5	3
6	Subcell Debye behavior analysis of orderâ€“disorder effects in triple-junction InGaP-based photovoltaic solar cells. <i>Journal of Luminescence</i> , 2015, 168, 309-314.	1.5	2
7	Characterization of the porous anodic alumina nanostructures with a metal interlayer on Si substrates. <i>Journal of Luminescence</i> , 2014, 148, 285-289.	1.5	2
8	Enhancement of exciton radiative recombination for In-doped ZnO nanowires with aluminum cylindrical micropillars. <i>Journal of Luminescence</i> , 2013, 136, 11-16.	1.5	3
9	Lie Group Analysis of the Photo-Induced Fluorescence of Drosophila Oogenesis with the Asymmetrically Localized Gurken Protein. <i>PLoS ONE</i> , 2013, 8, e65143.	1.1	2
10	Anomalous luminescence phenomena of indium-doped ZnO nanostructures grown on Si substrates by the hydrothermal method. <i>Nanoscale Research Letters</i> , 2012, 7, 270.	3.1	13
11	The effect of junction temperature on the optoelectrical properties of InGaN/GaN multiple quantum well light-emitting diodes. <i>Journal of Luminescence</i> , 2012, 132, 429-433.	1.5	15
12	Characterization of Nanocrystallites of InGaN/GaN Multiquantum Wells by High-Resolution X-ray Diffraction. <i>IEEE Nanotechnology Magazine</i> , 2011, 10, 827-831.	1.1	5
13	Lie group study of Raman spectra of the Gurken gradient in Drosophila oogenesis. <i>Analytical and Bioanalytical Chemistry</i> , 2011, 400, 335-341.	1.9	1
14	Carrier localization effect on luminescence spectra of IIIâ€“V heterostructures. <i>Journal of Luminescence</i> , 2011, 131, 1267-1271.	1.5	20
15	Characterization of temperature-dependent carrier transport in disordered indium-tin-oxide/poly(3,4-ethylenedioxythiophene):poly(styrenesulfonate)/polyfluorene/Ca/Al polymer structures. <i>Thin Solid Films</i> , 2011, 519, 4148-4151.	0.8	1
16	Characterization of high quality ZnO nanowire surface plasmon resonance sensors on Si substrate with perforated aluminum cylindrical micropillar arrays. , 2010, , .		0
17	Exciton wavefunction coupled surface plasmon resonance for In-rich InGaN film with perforated aluminum cylindrical micropillar arrays. <i>Microelectronics Reliability</i> , 2010, 50, 1107-1110.	0.9	2
18	Anomalous disorder-related phenomena in InGaN/GaN multiple quantum well heterosystems. <i>Journal of Luminescence</i> , 2010, 130, 1000-1004.	1.5	2

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19	Anomalous temperature-dependent behaviors of electroluminescence phenomena in disordered ITO/PEDOT/PF/Ca/Al polymer light-emitting diodes. <i>Journal of Luminescence</i> , 2010, 130, 1802-1804.	1.5	2
20	Performance enhancements in optoelectrical properties of InGaN/GaN light-emitting diodes with micro-hole arrayed indium-tin-oxide layer. , 2010, , .		0
21	Anomalous disordered-related phenomena in the InGaN/GaN multiple quantum well heterosystems. , 2009, , .		0
22	Bias dependence of phonon behaviors in the InGaN/GaN multiple quantum well with multiquantum barriers. , 2009, , .		0
23	Characterization of the anomalous luminescence properties from self-ordered porous anodic alumina with oxalic acid electrolytes. <i>Thin Solid Films</i> , 2009, 518, 1439-1442.	0.8	15
24	Optical investigations of Berthelot-type properties in quaternary AlInGaN multiple quantum well heterosystems. <i>Journal of Crystal Growth</i> , 2009, 311, 3544-3548.	0.7	0
25	Anomalous excitation dependence of electroluminescence in InGaN ⁺ GaN light-emitting diodes. <i>Journal of Applied Physics</i> , 2007, 101, 023703.	1.1	6
26	The dependence of excitonic characteristics on the interface charge distribution with multiquantum barrier. , 2007, , .		0
27	Intersublevel relaxation properties of self-assembled InAs/GaAs quantum dot heterostructures. , 2007, , .		0
28	Temperature and Excitation Dependence of Photoluminescence Spectra of InAs/GaAs Quantum Dot Heterostructures. <i>IEEE Nanotechnology Magazine</i> , 2007, 6, 492-496.	1.1	6
29	Effect of multiquantum barriers on performance of InGaN ⁺ GaN multiple-quantum-well light-emitting diodes. <i>Journal of Applied Physics</i> , 2007, 102, 033101.	1.1	6
30	Characterization of interface fluctuations and emission mechanisms in InGaN/AlGaIn multiple quantum wells. <i>Physica B: Condensed Matter</i> , 2007, 401-402, 568-571.	1.3	0
31	Improvements of quantum efficiency and thermal stability by using Si delta doping in blue InGaN/GaN multiple quantum well light-emitting diodes. <i>Physica Status Solidi C: Current Topics in Solid State Physics</i> , 2007, 4, 2797-2801.	0.8	4
32	Characterization of Berthelot-type behaviors of InGaN/GaN semiconductor heterosystems. <i>Journal of Crystal Growth</i> , 2006, 287, 468-471.	0.7	13
33	Thermally Activated Carrier Dynamics and Photoluminescence in Self-assembled InAs Quantum Dots. , 2006, , .		0
34	Cross sections for the investigation of the electroluminescence excitation of InGaN ⁺ GaN quantum wells in blue light-emitting diodes with multiquantum barriers. <i>Journal of Vacuum Science & Technology an Official Journal of the American Vacuum Society B, Microelectronics Processing and Phenomena</i> , 2005, 23, 966.	1.6	10
35	Characterization of the carrier confinement for InGaN/GaN light emitting diode with multiquantum barriers. <i>Materials Research Society Symposia Proceedings</i> , 2004, 831, 406.	0.1	0